

Silicon NPN Power Transistors

2SC3679

DESCRIPTION

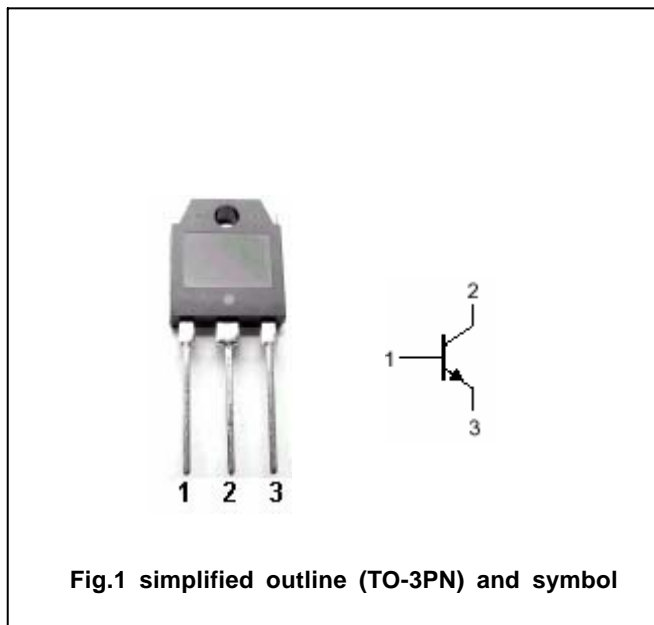
- With TO-3PN package
- High voltage switching transistor

APPLICATIONS

- For switching regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		5	A
I_{CM}	Collector current -peak		10	A
I_B	Base current (DC)		2.5	A
P_C	Collector power dissipation	$T_C=25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	800			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =800V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =4V	10		30	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		6		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		75		pF

Switching times

t _{on}	Turn-on time	I _C =2.0A I _{B1} =0.3A, I _{B2} =-1A V _{CC} =250V, R _L =125			1.0	μs
t _s	Storage time				5.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

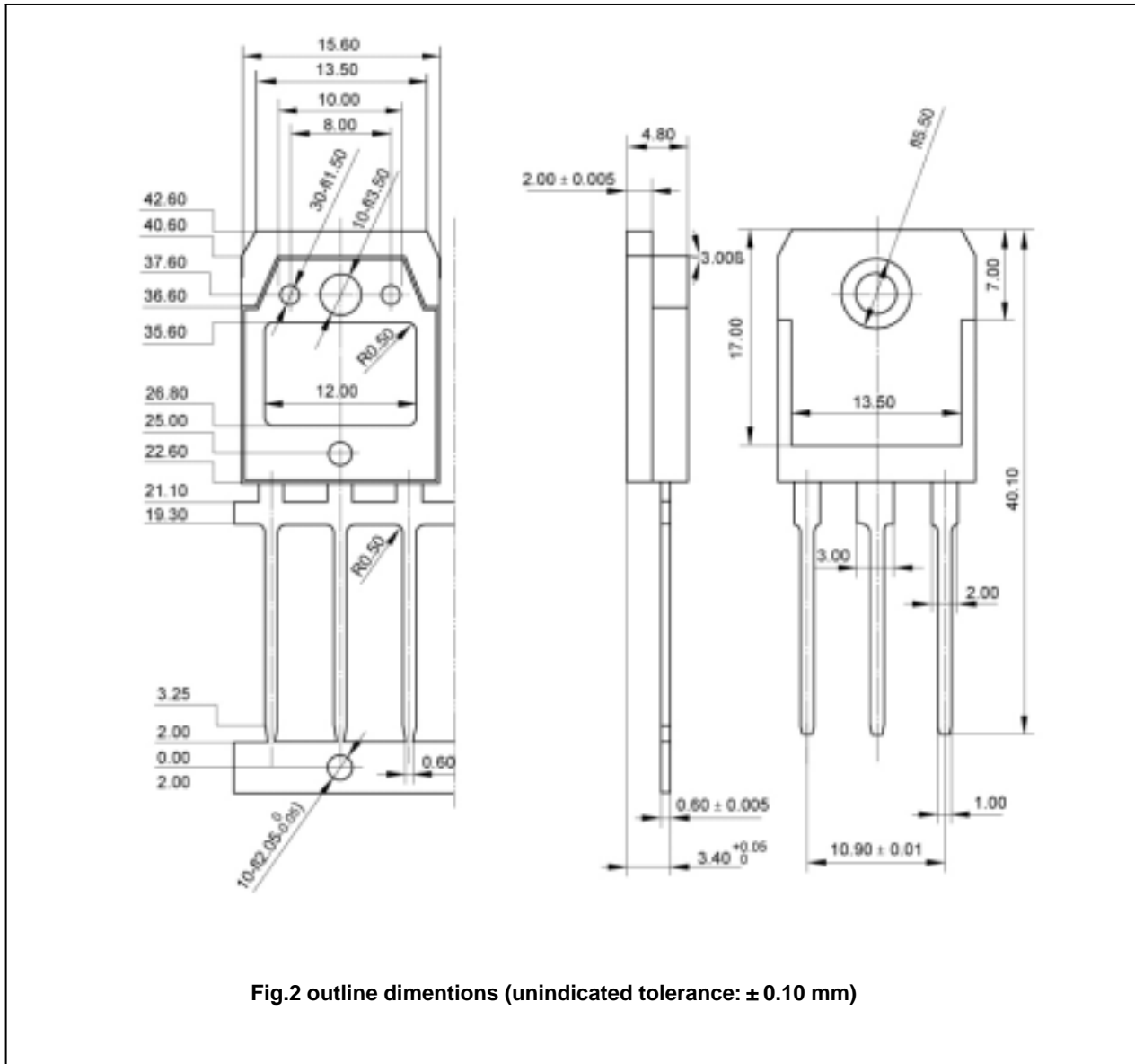


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)

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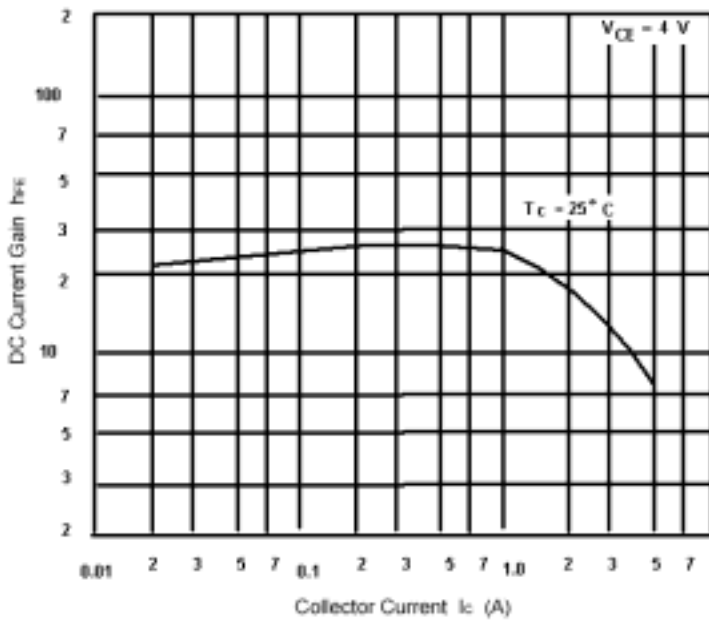


Fig.3 DC current Gain

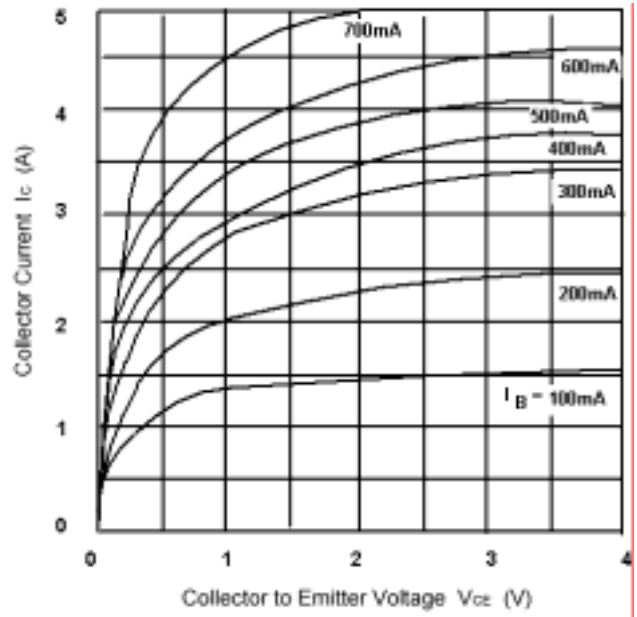


Fig.4 Static Characteristic

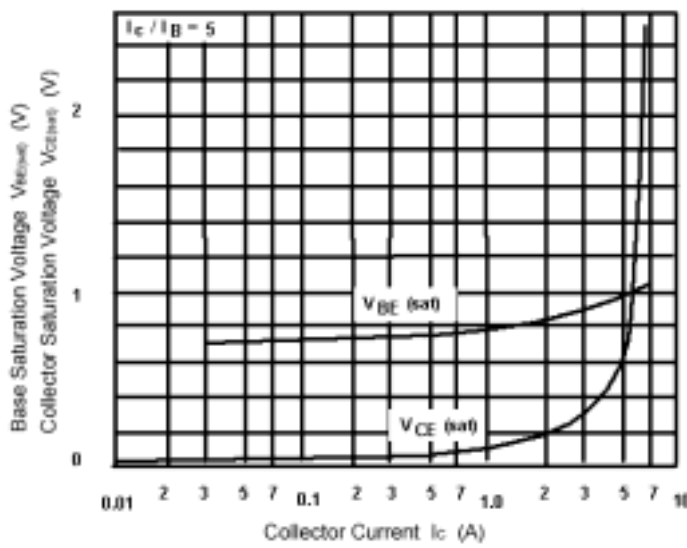


Fig.5 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

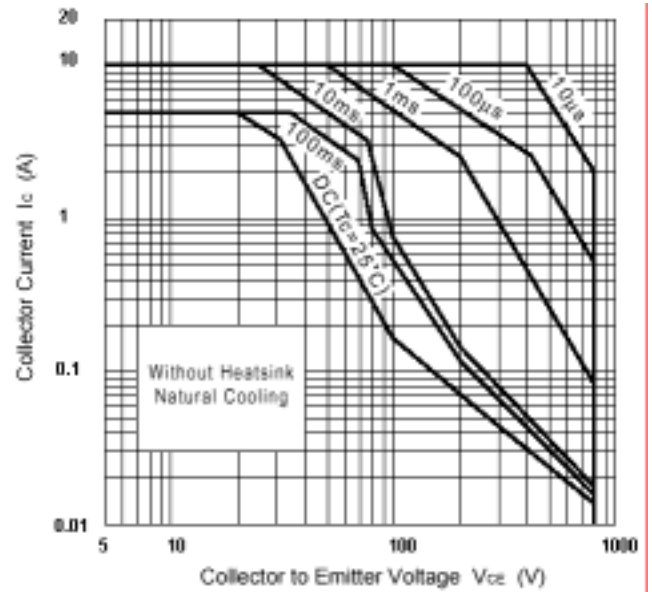


Fig.6 Safe Operating Area